

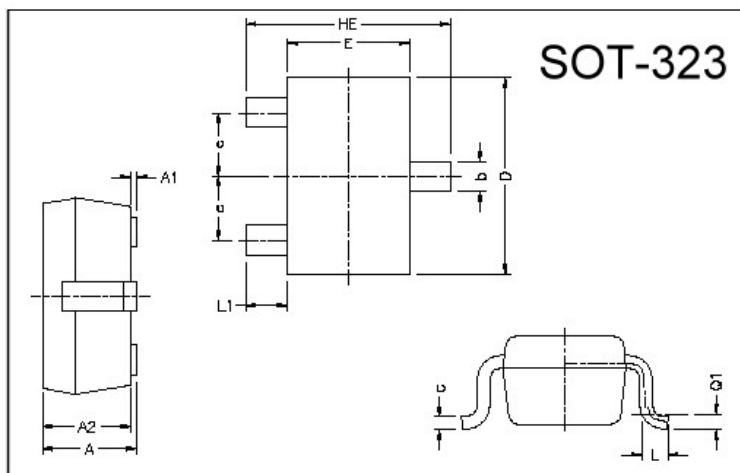
GS420SD

SURFACE MOUNT, SCHOTTKY BARRIER DIODE
VOLTAGE 40V, CURRENT 0.1A

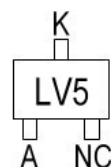
Description

The GS420SD is designed for low power rectification.

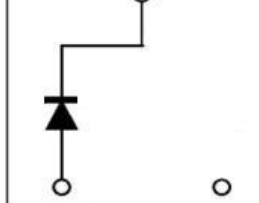
Package Dimensions



Marking :



Circuit :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.80	1.10	L1	0.42 REF.	
A1	0	0.10	L	0.15	0.35
A2	0.80	1.00	b	0.25	0.40
D	1.80	2.20	c	0.10	0.25
E	1.15	1.35	e	0.65 REF.	
HE	1.80	2.40	Q1	0.15 BSC.	

Absolute Maximum Ratings at TA = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+125	°C
Storage Temperature	Tstg	-40 ~ +125	°C
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	40	V
Maximum RMS Voltage	V _{RMS}	28	V
Maximum DC Blocking Voltage	V _{DC}	40	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I _{FSM}	1.0	A
Typical Junction Capacitance between Terminal (Note 1)	C _J	6.0	pF
Maximum Average Forward Rectified Current	I _O	0.1	A
Total Power Dissipation	PD	225	mW

Electrical Characteristics (at TA = 25°C unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	V _{(BR)R}	40	-	-	V	IR=100μA
Maximum Instantaneous Forward Voltage	V _F	-	-	450	mV	IF=10mA
Maximum Average Reverse Current	I _R	-	-	1.0	uA	VR=10V

Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 10 volts.

2. ESD sensitive product handling required.

Characteristics Curve

FIG. 1 - FORWARD CHARACTERISTICS

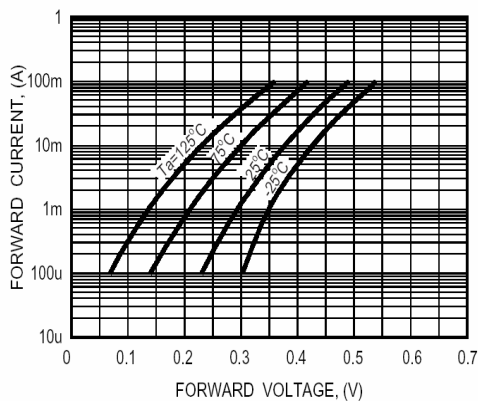


FIG. 2 - REVERSE CHARACTERISTICS

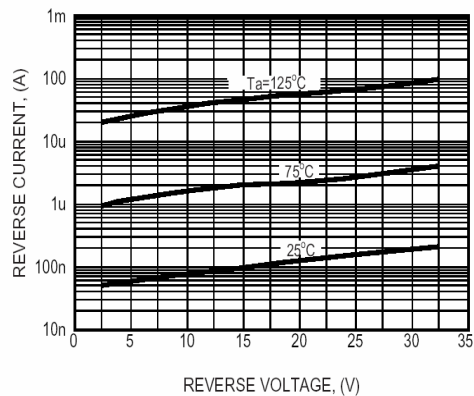


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

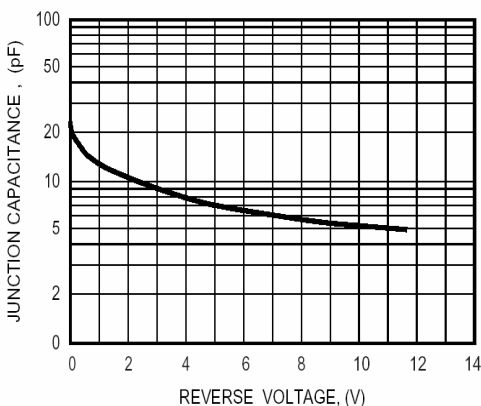


FIG. 4 - FORWARD POWER DISSIPATION CHARACTERISTICS

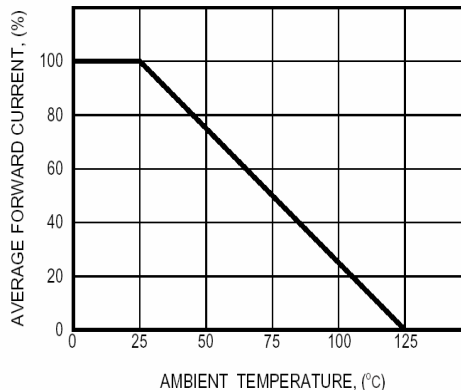
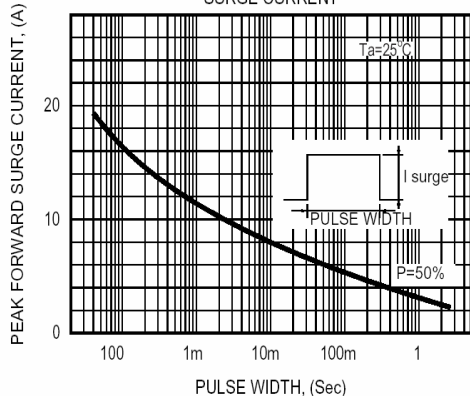


FIG. 5 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT



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